

AMENDMENTS**In the claims:**

Please amend claims 48-50 and 57 as follows:

48. (Once Amended) A semiconductor substrate according to claim 25, wherein the n-th and (n+1)-th patterned masks are formed of the same material.

E1 49. (Once Amended) A semiconductor substrate according to claim 27, wherein the n-th and (n+1)-th patterned masks are formed of the same material.

50. (Once Amended) A semiconductor substrate according to claim 37, wherein the n-th and (n+1)-th patterned masks are formed of the same material.

57. (Once Amended) A semiconductor substrate comprising:
an n-th patterned mask containing a material having a growth suppressing effect,
provided on or above a lower substrate, wherein n is an integer of 1 or more;
an n-th nitride semiconductor crystal layer grown on or above the lower substrate via the n-th mask; and

E2 an (n+1)-th patterned mask containing a material having a growth suppressing material substantially provided above an opening of the n-th patterned mask; and an (n+1)-th nitride semiconductor crystal layer grown on or above the lower substrate via the (n+1)-th patterned mask,

wherein the n-th patterned mask and the (n+1)-th patterned mask are respectively patterned in a stripe shape; and

wherein the stripe width of the (n+1)-th patterned mask is the same as that of the n-th patterned mask or is smaller than a size of the respective opening of the n-th patterned mask.